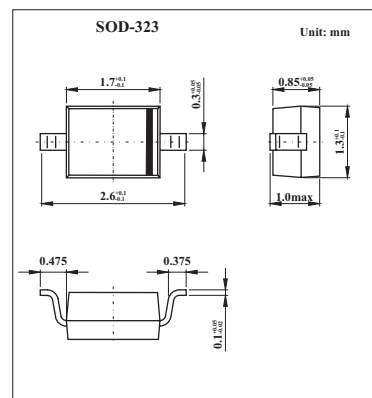


Silicon Schottky Diode

BAT14-03W

■ Features

- DBS mixer application to 12GHz
- Medium barrier type
- Low capacitance

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	4	V
Forward current	I_F	90	mA
Operating temperature range	T_{op}	-55 to +125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	
Total power dissipation $T_s \leq 85^\circ\text{C}$	P_{tot}	100	mW
Junction ambient ⁽¹⁾	R_{thJA}	≤ 450	$^\circ\text{C}$
Junction-soldering point	R_{thJS}	≤ 690	K/W

Note:

1. Package mounted on an epoxy pcb 40 mm × 40 mm × 15 mm/1cm² Cu.

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min	Typ	Max	Unit
Breakdown Voltage $I_{(BR)} = 5 \mu\text{A}$	$V_{(BR)}$	4			V
Forward voltage $I_F = 1 \text{ mA}$ $I_F = 10 \text{ mA}$	V_F	0.36	0.43	0.52	V
		0.48	0.55	0.66	
Diode capacitance $V_R = 0; f = 1 \text{ MHz}$	C_T		0.22	0.35	pF
Differential forward resistance $I_F = 10 \text{ mA}/50 \text{ mA}$	R_F		5.5		Ω

■ Marking

Marking	O
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